

## PSMN2R2-40BS

# N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK Rev. 1 — 20 March 2012 Product data

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### 1.3 Applications

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
$I_D$	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see Figure 1	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static char	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 100 \text{ °C;}$ see Figure 6		-	2.73	3.2	mΩ
		$V_{GS} = 10 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 6</u> ; see <u>Figure 13</u>		-	1.88	2.2	mΩ
Dynamic c	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 20 \text{ V};$		-	25	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	130	-	nC
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 40 V; unclamped; $R_{GS}$ = 50 $\Omega$		-	-	1.24	J

<sup>[1]</sup> Continuous current is limited by package



## 2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	drain		mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make connection to pin 2

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R2-40BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN2R2-40BS	PSMN2R2-40BS

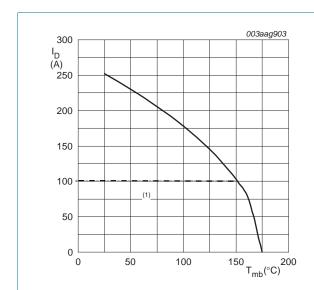
## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	40	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$ ; see Figure 3		-	962	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	306	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dr	ain diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	962	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 40 V; unclamped; $R_{GS}$ = 50 $\Omega$		-	1.24	J

#### [1] Continuous current is limited by package



 $V_{GS} \ge 10 \text{ V}$ ; (1) Capped at 100 A due to package

Fig 1. Continuous drain current as a function of mounting base temperature.

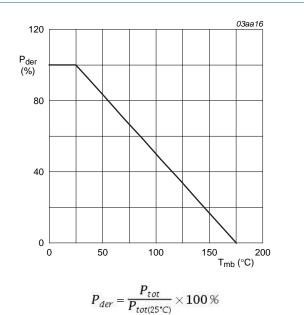
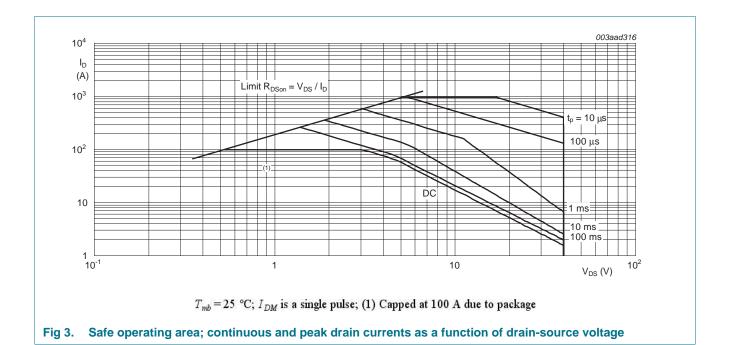


Fig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN2R2-40BS



## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.25	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum foot print; mounted in a printed circuit board	-	50	-	K/W

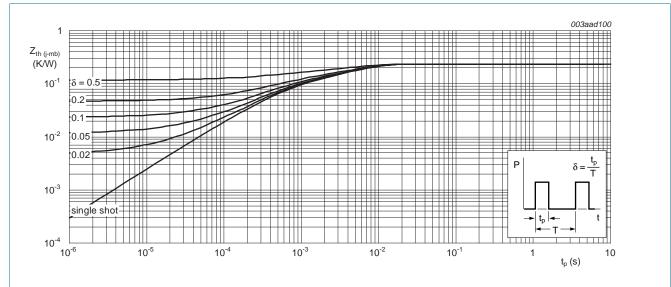


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 7. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	36	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see Figure 11	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 11	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	200	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R <sub>DSon</sub> drain-source on-state resistan	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 6	-	2.73	3.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 13; see Figure 6	-	3.76	4.4	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 6; see Figure 13	-	1.88	2.2	mΩ	
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic o	characteristics					
Q <sub>G(tot)</sub> total gate charge		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	110	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	130	-	nC
$Q_{GS}$	gate-source charge	see Figure 14; see Figure 15	-	42	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	24	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	18	-	nC
$Q_{GD}$	gate-drain charge		-	25	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; see Figure 14; see Figure 15	-	4.95	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	8423	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	1671	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	814	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $R_L$ = 0.25 $\Omega$ ; $V_{GS}$ = 10 V;	-	33.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 1.5 \Omega$	-	40.4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	66.6	-	ns
t <sub>f</sub>	fall time		-	25.2	-	ns

 Table 7.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 17</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$	-	53.7	-	ns
Q <sub>r</sub>	recovered charge	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $T_j = 25 \text{ °C}$	-	80.75	-	nC

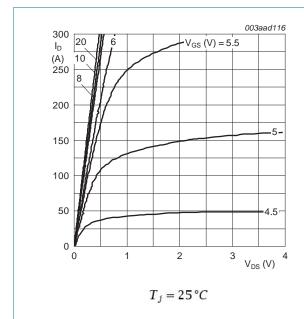


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

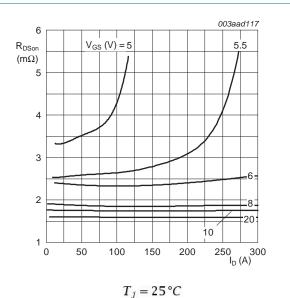


Fig 6. Drain-source on-state resistance as a function of drain current; typical values

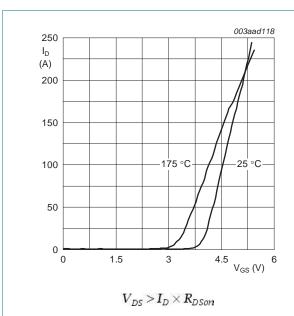


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

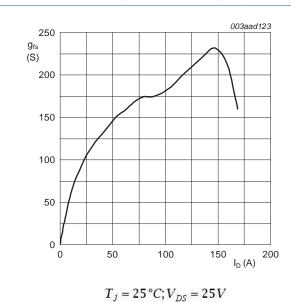
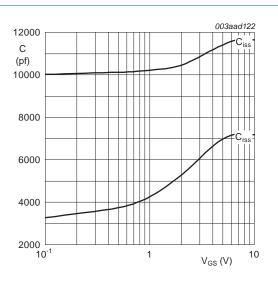
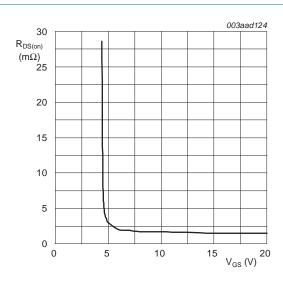


Fig 9. Forward transconductance as a function of drain current; typical values



$$V_{DS} = 0V; f = 1MHz$$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25$  °C;  $I_D = 25$  A

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

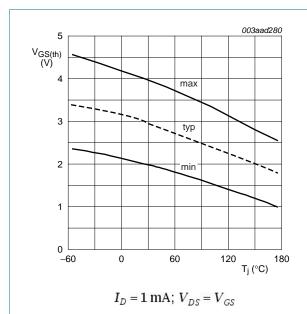
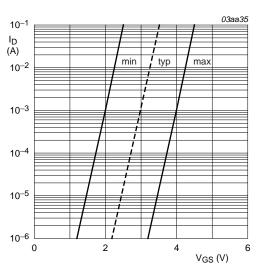


Fig 11. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 

Fig 12. Sub-threshold drain current as a function of gate-source voltage

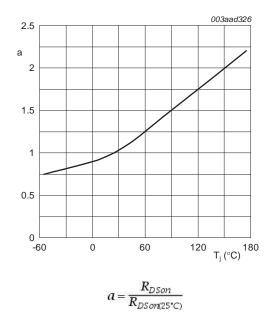


Fig 13. Normalized drain-source on state resistance factor as a function of junction temperature

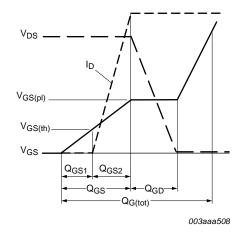


Fig 14. Gate charge waveform definitions

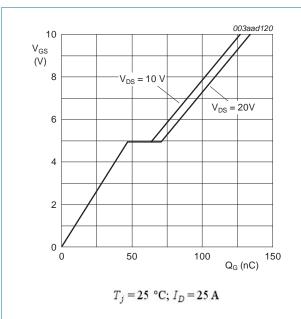
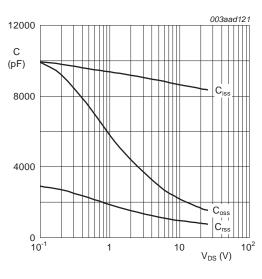
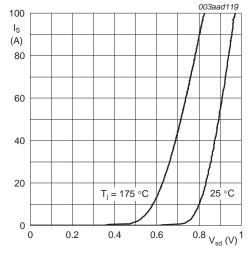


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0V$ 

Fig 17. Source current as a function of source-drain voltage; typical values

## 8. Package outline

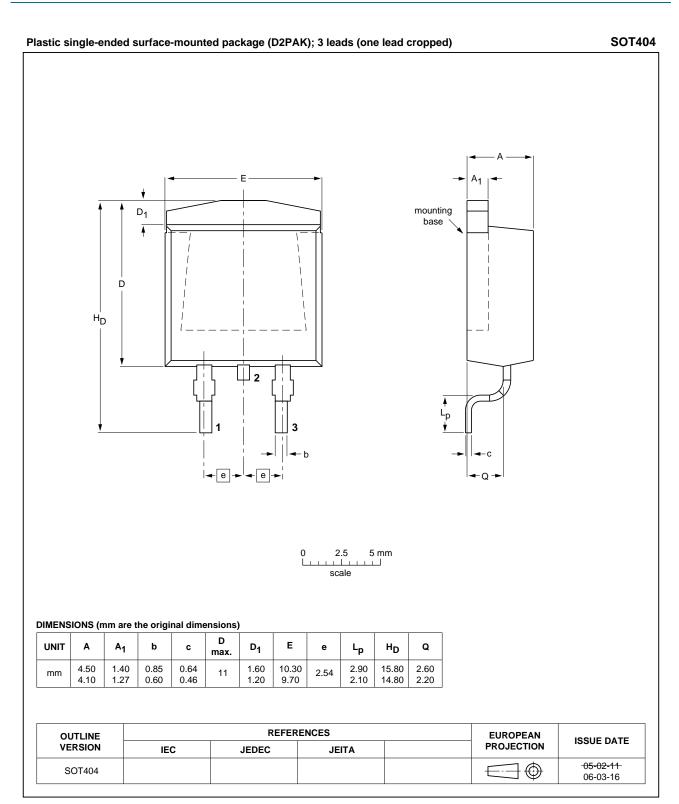


Fig 18. Package outline SOT404 (D2PAK)

## 9. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R2-40BS v.1	20120320	Product data sheet	-	-

## 10. Legal information

#### 10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## PSMN2R2-40BS

#### N-channel 40 V 2.2 mΩ standard level MOSFET in D2PAK

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## 12. Contents

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